

N-channel 60 V 7.8 mΩ standard level MOSFET

Rev. 03 — 28 October 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions	Min	Тур	Мах	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	60	V
drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	-	-	92	A
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	149	W
acteristics					
drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \ ^{\circ}\text{C}; \text{ see } \underline{\text{Figure } 13}; \\ \text{see } \underline{\text{Figure } 9} \end{array}$	-	5.9	7.8	mΩ
naracteristics					
gate-drain charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ V_{DS} = 30 \text{ V}; \text{ see } \underline{\text{Figure 15}}; \\ \text{see } \underline{\text{Figure 14}} \end{array}$	-	10.6	-	nC
ruggedness					
non-repetitive drain-source avalanche energy		-	-	110	mJ
	drain-source voltage drain current total power dissipation acteristics drain-source on-state resistance maracteristics gate-drain charge ruggedness non-repetitive drain-source avalanche	drain-source voltage $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$ drain current $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see Figure 1total power dissipation $T_{mb} = 25 \text{ °C};$ see Figure 2acteristicsdrain-source on-state resistance $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 13; see Figure 9maracteristicsgate-drain charge $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 30 \text{ V};$ see Figure 15; see Figure 14ruggednessnon-repetitive drain-source avalanche $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $I_D = 92 \text{ A}; V_{sup} \le 100 \text{ V};$	$\begin{array}{ll} \mbox{drain-source voltage} & T_j \geq 25 \ {}^\circ\mbox{C}; \ T_j \leq 175 \ {}^\circ\mbox{C} & - \\ \mbox{drain current} & T_{mb} = 25 \ {}^\circ\mbox{C}; \ V_{GS} = 10 \ V; & - \\ \mbox{see Figure 1} & & \\ \mbox{total power dissipation} & T_{mb} = 25 \ {}^\circ\mbox{C}; \ \mbox{see Figure 2} & - \\ \mbox{acteristics} & & \\ \mbox{drain-source on-state} & V_{GS} = 10 \ V; \ I_D = 25 \ A; & - \\ \ T_j = 25 \ {}^\circ\mbox{C}; \ \mbox{see Figure 13}; & \\ \mbox{see Figure 9} & & \\ \mbox{aracteristics} & & \\ \mbox{gate-drain charge} & V_{GS} = 10 \ V; \ I_D = 25 \ A; & - \\ \ V_{DS} = 30 \ V; \ \mbox{see Figure 15}; & \\ \mbox{see Figure 14} & & \\ \mbox{ruggedness} & \\ \mbox{non-repetitive} & V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ {}^\circ\mbox{C}; & - \\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	drain-source voltage $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$ -drain current $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ -drain current $T_{mb} = 25 \text{ °C}; \text{ see Figure 2}$ -total power dissipation $T_{mb} = 25 \text{ °C}; \text{ see Figure 2}$ -acteristicsdrain-source on-state $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ -resistance $T_j = 25 \text{ °C}; \text{ see Figure 13};$ see Figure 9maracteristicsgate-drain charge $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ - $V_{DS} = 30 \text{ V}; \text{ see Figure 15};$ see Figure 15;-see Figure 14ruggednessnon-repetitive $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ - $I_D = 92 \text{ A}; V_{sup} \le 100 \text{ V};$ -	drain-source voltage $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$ 60drain current $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see Figure 192total power dissipation $T_{mb} = 25 \text{ °C};$ see Figure 2149acteristicsdrain-source on-state resistance $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 13; see Figure 9-5.97.8aracteristicsgate-drain charge $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 30 \text{ V};$ see Figure 15; see Figure 14-10.6-ruggednessnon-repetitive drain-source avalanche $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $I_D = 92 \text{ A}; V_{sup} \le 100 \text{ V};$ -110

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN7R6-60PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

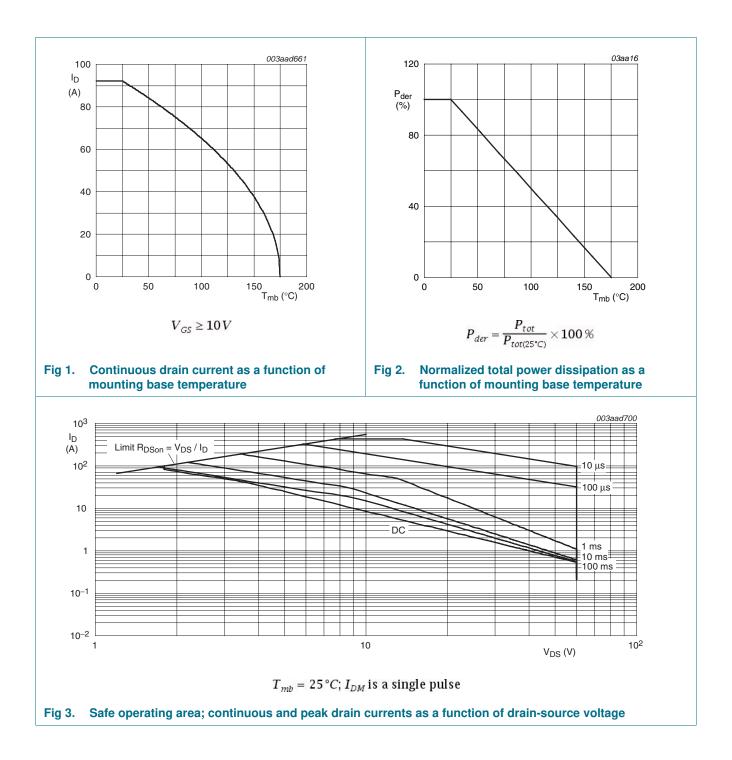
Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	60	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	60	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	65	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	92	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	389	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	149	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	92	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	389	А
Avalanche i	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 92 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω ; unclamped	-	110	mJ

PSMN7R6-60	PS	
Product	data	sheet

PSMN7R6-60PS



10⁻²

10⁻³

Fig 4.

10⁻⁶

PSMN7R6-60PS

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t

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tp

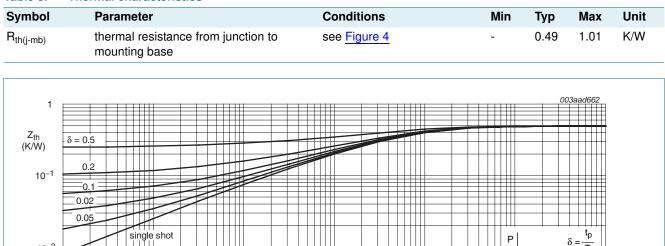
t_p (s)

10⁻¹

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5. Thermal characteristics

10⁻⁵



Transient thermal impedance from junction to mounting base as a function of pulse duration

10⁻³

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10⁻⁴

10-2

Table 5. Thermal characteristics

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6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	54	-	-	V
		$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 10; see Figure 11	2	3	4	V
V _{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 11</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	4.6	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u>	-	13.3	18	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13; see Figure 9	-	5.9	7.8	mΩ
R _G	gate resistance	f = 1 MHz	-	0.98	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$	-	38.7	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	12.9	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	6.9	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	6	-	nC
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 15; see Figure 14	-	10.6	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; \text{ see } \frac{\text{Figure}}{14}; \text{ see } \frac{\text{Figure } 15}{15}$	-	5.6	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 16}}{\text{Figure 8}}; \text{ see}$	-	2651	-	pF
C _{oss}	output capacitance	$\label{eq:VDS} \begin{array}{l} V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; \text{f} = 1 \text{ MHz}; \\ T_{j} = 25 ^{\circ}\text{C}; \text{ see } \underline{\text{Figure 16}} \end{array}$	-	342	-	pF
S _{rss}	reverse transfer capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 16}}{\text{Figure 8}}; \text{ see}$	-	183	-	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	19	-	ns
r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	21	-	ns
d(off)	turn-off delay time		-	37	-	ns
t _f	fall time		-	13	-	ns

Symbol

PSMN7R6-60PS

Max

Unit

Тур

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Min

ource-drai	n diode					
SD	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.86	1.2	V
	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s};$	-	40.4	-	ns
r	recovered charge	V_{GS} = 0 V; V_{DS} = 30 V	-	56	-	nC
100	C	003aad663			03aad669	
ID	15 11 6.0	06				
(A)	10 5.5	6 (S)				
80 -		120				
				\neg		
60						
	5.0	80 80				
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20 —		40				
	$V_{GS}(V) = 4.5$					
。						
	$T_j = 25$ °C; $t_p = 300 \ \mu s$ tput characteristics: drain cu	v _{DS} (V) ² 0 20 Irrent as a Fig 6. Forward t	40 60 ransconductar	nce as a	I _D (A)	
ig 5. Ou	$T_j = 25 ^{\circ}\text{C}; t_p = 300 \mu s$	v _{DS} (V) ² 0 20 Irrent as a Fig 6. Forward t		nce as a	I _D (A)	
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-ig 5. Ou	$T_j = 25$ °C; $t_p = 300 \ \mu s$ tput characteristics: drain cu iction of drain-source voltage	V _{DS} (V) ² 0 20 Fig 6. Forward t drain curr 003aad665 11 4000	ransconductar	nce as a lues	I _D (A)	
Fig 5. Ou fun 100 I _D (A)	$T_j = 25$ °C; $t_p = 300 \ \mu s$ tput characteristics: drain cu iction of drain-source voltage	V _{DS} (V) ² 0 20 Irrent as a b; typical values VDS (V) ² Fig 6. Forward t drain curr 4000	ransconductar	nce as a lues	I _D (A)	
Fig 5. Ou fun	$T_j = 25$ °C; $t_p = 300 \ \mu s$ tput characteristics: drain cu iction of drain-source voltage	V _{DS} (V) ² 0 20 Fig 6. Forward t drain curr 003aad665 4000 C	ransconductar	nce as a lues	I _D (A)	
Fig 5. Ou fun	$T_j = 25$ °C; $t_p = 300 \ \mu s$ tput characteristics: drain cu iction of drain-source voltage	V _{DS} (V) ² 0 20 Fig 6. Forward t drain curr 003aad665 4000 C (pF) C Ciss	ransconductar	nce as a lues	I _D (A)	
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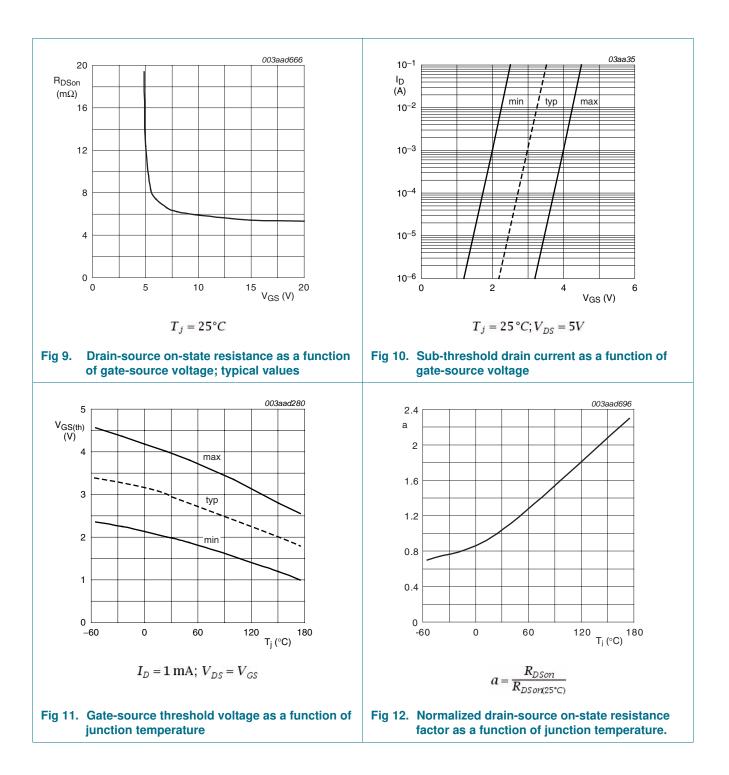
Conditions

Table 6. Characteristics ...continued

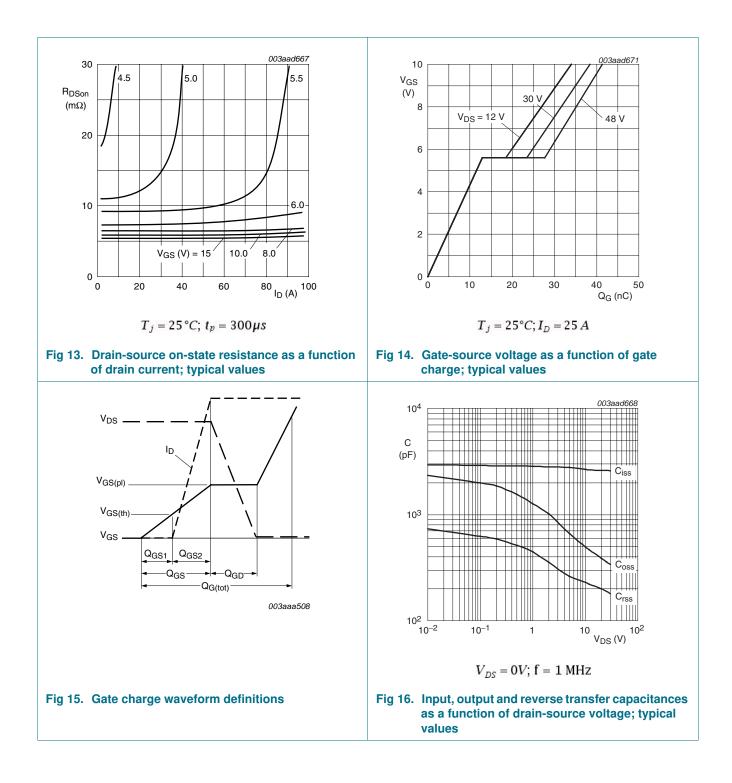
Parameter

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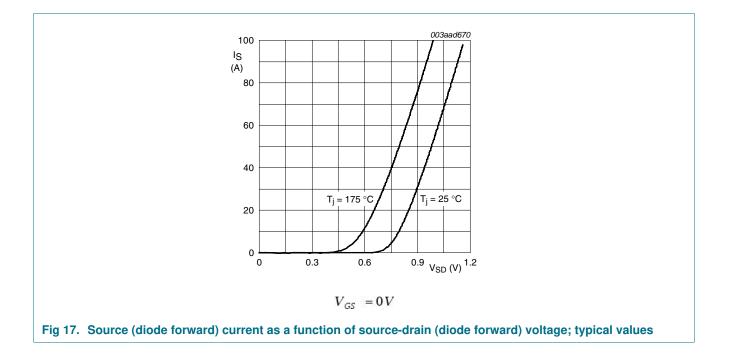
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Package outline 7.

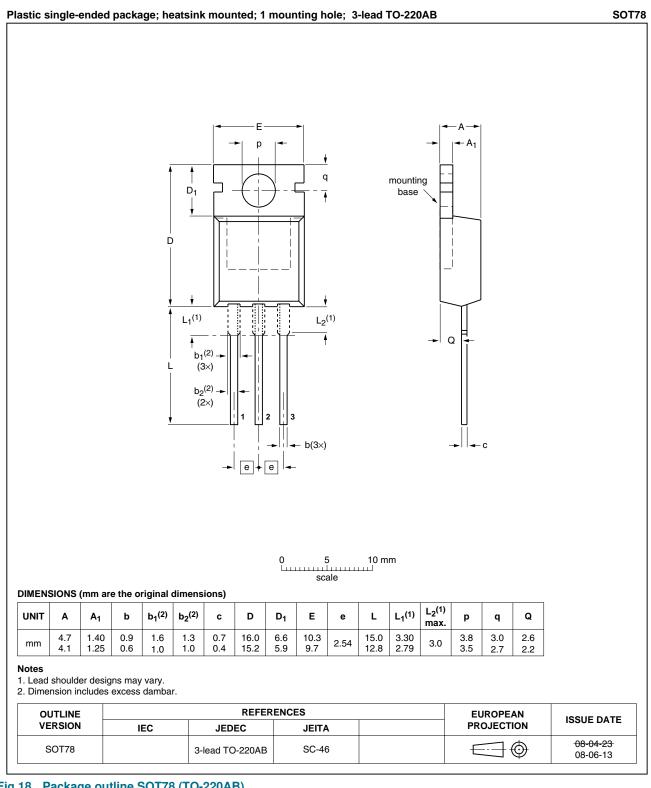


Fig 18. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7.Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R6-60PS v.3	20101028	Product data sheet	-	PSMN7R6-60PS v.2
Modifications:	Various change	s to content.		
PSMN7R6-60PS v.2	20100122	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

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10. Contact information

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